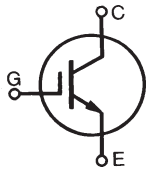
IXYS

1200V XPT™ IGBT GenX3™

IXYH40N120C3

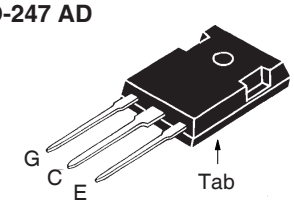
V_{CES} = 1200V
I_{C110} = 40A
$V_{CE(sat)}$ ≤ 3.5V
$t_{fi(typ)}$ = 50ns

High-Speed IGBT
for 20-50 kHz Switching



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	T_J = 25°C to 175°C	1200	V
V_{CGR}	T_J = 25°C to 175°C, R_{GE} = 1MΩ	1200	V
V_{GES}	Continuous	±20	V
V_{GEM}	Transient	±30	V
I_{C25}	T_C = 25°C (Chip Capability)	90	A
I_{C110}	T_C = 110°C	40	A
I_{CM}	T_C = 25°C, 1ms	175	A
I_A	T_C = 25°C	20	A
E_{AS}	T_C = 25°C	400	mJ
SSOA (RBSOA)	V_{GE} = 15V, T_{VJ} = 150°C, R_G = 10Ω Clamped Inductive Load	I_{CM} = 80 @$V_{CE} \leq V_{CES}$	A
P_C	T_C = 25°C	577	W
T_J		-55 ... +175	°C
T_{JM}		175	°C
T_{stg}		-55 ... +175	°C
T_L	Maximum Lead Temperature for Soldering	300	°C
T_{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M_d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD



G = Gate C = Collector
E = Emitter Tab = Collector

Features

- Optimized for Low Switching Losses
- Square RBSOA
- Positive Thermal Coefficient of Vce(sat)
- Avalanche Rated
- High Current Handling Capability
- International Standard Package

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

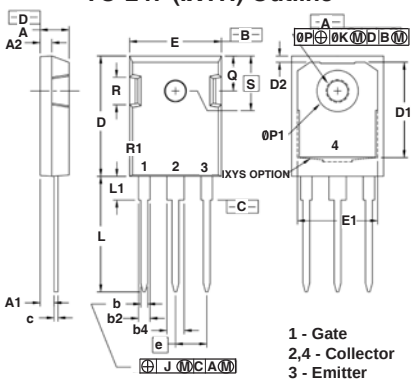
- High Frequency Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V	1200			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}	3.0		5.0	V
I_{CES}	V_{CE} = V_{CES}, V_{GE} = 0V			10	μA
	T_J = 150°C			750	μA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V			±100	nA
$V_{CE(sat)}$	I_C = 40A, V_{GE} = 15V, Note 1		2.9	3.5	V
	T_J = 150°C		3.7		V

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Symbol	Test Conditions (T_J = 25°C Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
g_{fs}	I_C = 40A, V_{CE} = 10V, Note 1	11	18	S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		1870	pF
C_{oes}			107	pF
C_{res}			38	pF
$Q_{g(on)}$	I_C = 40A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		80	nC
Q_{ge}			14	nC
Q_{gc}			37	nC
$t_{d(on)}$	**Inductive load, T_J = 25°C**		18	ns
t_{ri}	I_C = 40A, V_{GE} = 15V		64	ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 10Ω		3.8	mJ
$t_{d(off)}$	Note 2		133	ns
t_{fi}			50	ns
E_{off}			1.1	mJ
$t_{d(on)}$	**Inductive load, T_J = 150°C**		22	ns
t_{ri}	I_C = 40A, V_{GE} = 15V		73	ns
E_{on}	V_{CE} = 0.5 • V_{CES}, R_G = 10Ω		6.6	mJ
$t_{d(off)}$	Note 2		160	ns
t_{fi}			143	ns
E_{off}			2.1	mJ
R_{thJC}				0.26 °C/W
R_{thCS}			0.21	°C/W

TO-247 (IXYH) Outline



1 - Gate
2,4 - Collector
3 - Emitter

SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
øP	.140	.144	3.55	3.65
øP1	.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

Notes:

1. Pulse test, t ≤ 300µs, duty cycle, d ≤ 2%.
2. Switching times & energy losses may increase for higher V_{CE}(clamp), T_J or R_G.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,860,072 4,881,106 4,931,844 5,017,508 5,034,796 5,049,961 5,063,307 5,187,117 5,237,481 5,381,025 5,486,715 6,162,665 6,259,123 B1 6,306,728 B1 6,404,065 B1 6,534,343 6,583,505 6,683,344 6,710,405 B2 6,710,463 6,727,585 6,759,692 6,771,478 B2 7,005,734 B2 7,063,975 B2 7,071,537 7,157,338B2

Fig. 1. Output Characteristics @ T_J = 25ºC

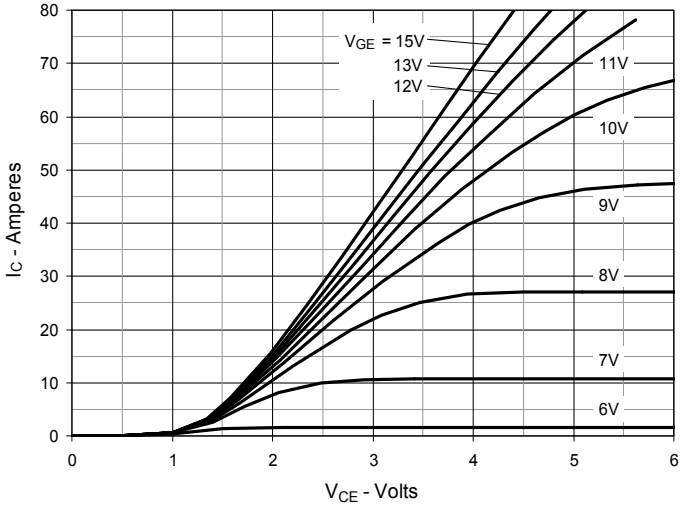


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

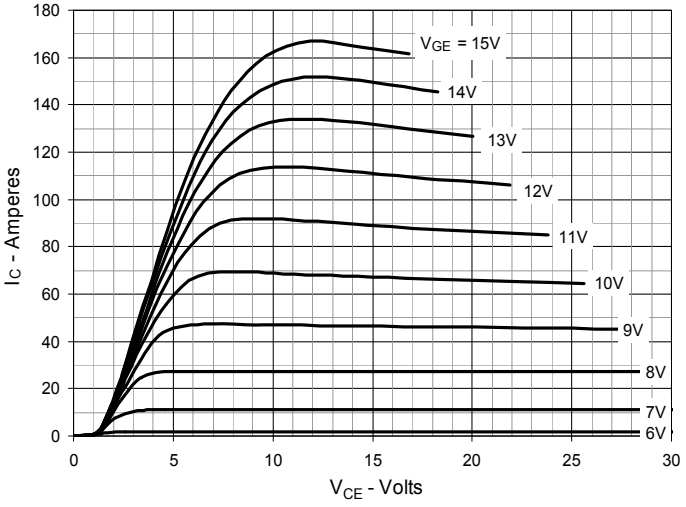


Fig. 3. Output Characteristics @ T_J = 150ºC

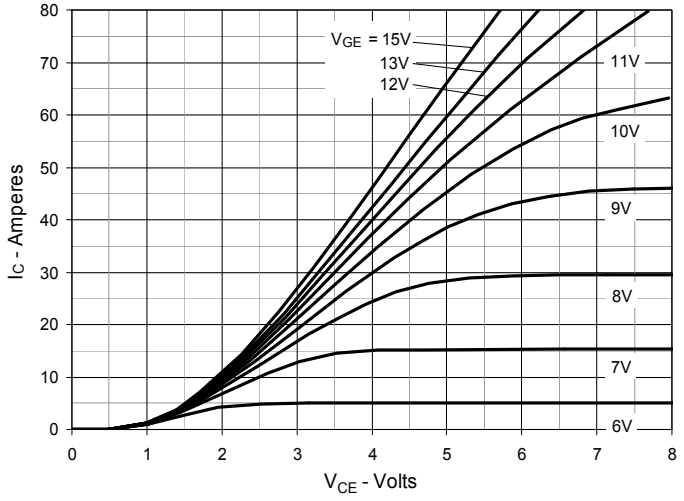


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

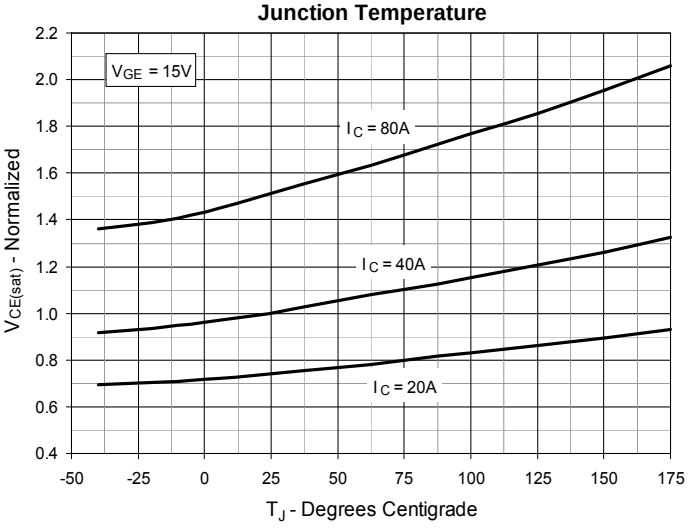


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

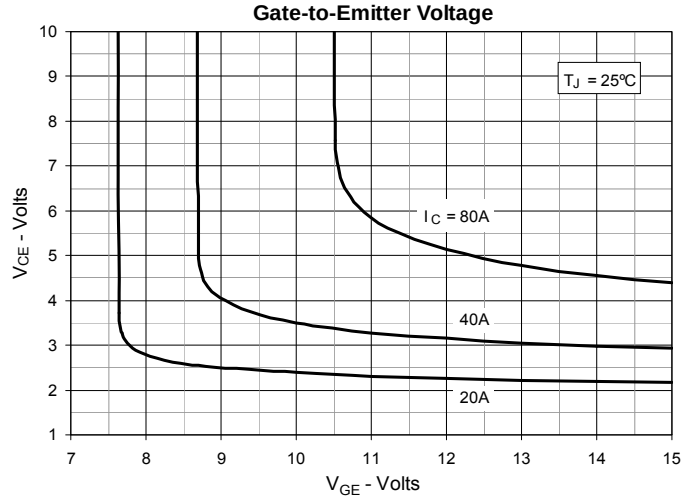
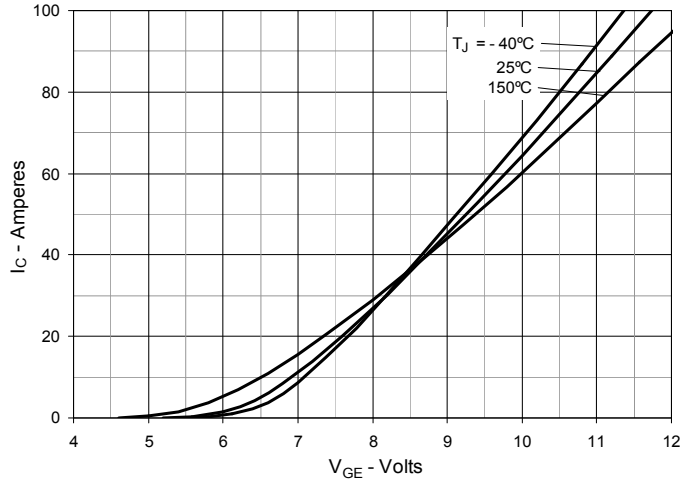


Fig. 6. Input Admittance



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Fig. 7. Transconductance

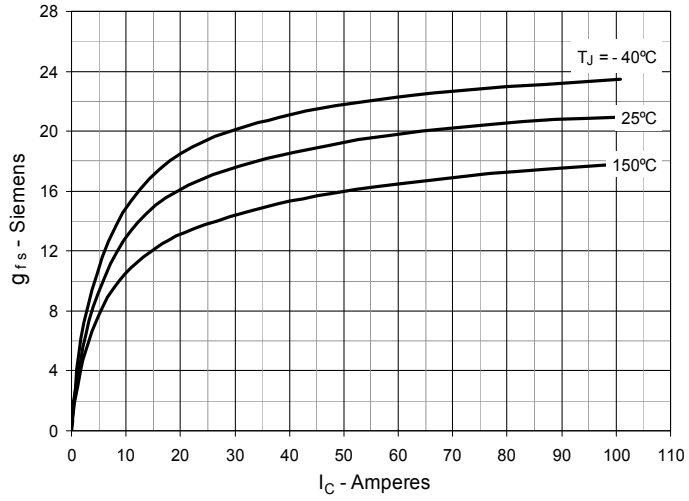


Fig. 8. Gate Charge

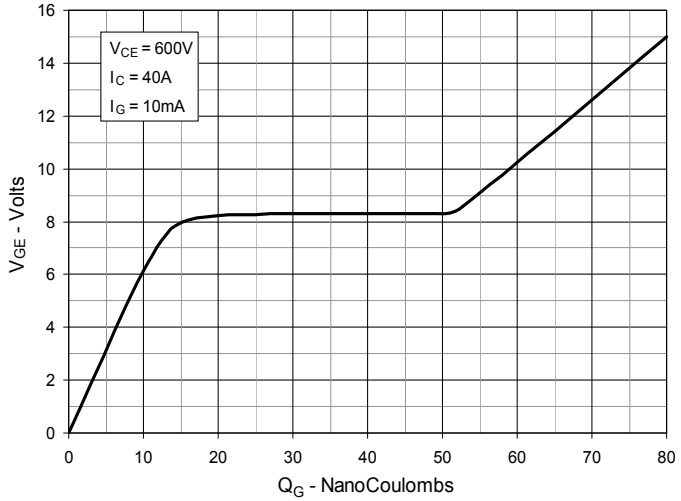


Fig. 9. Capacitance

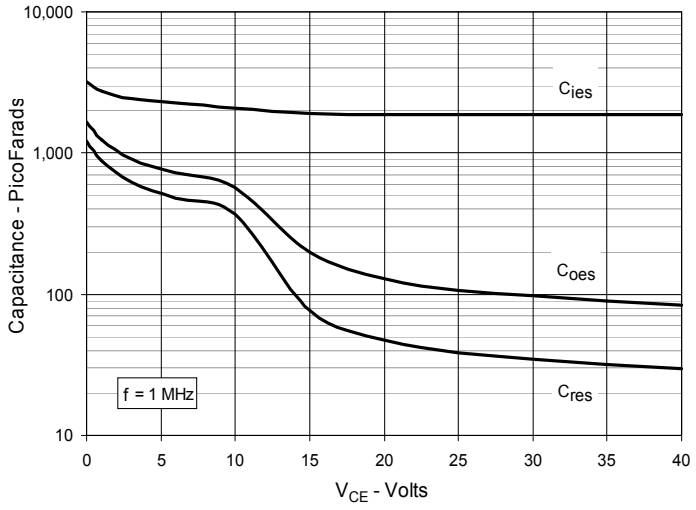


Fig. 10. Reverse-Bias Safe Operating Area

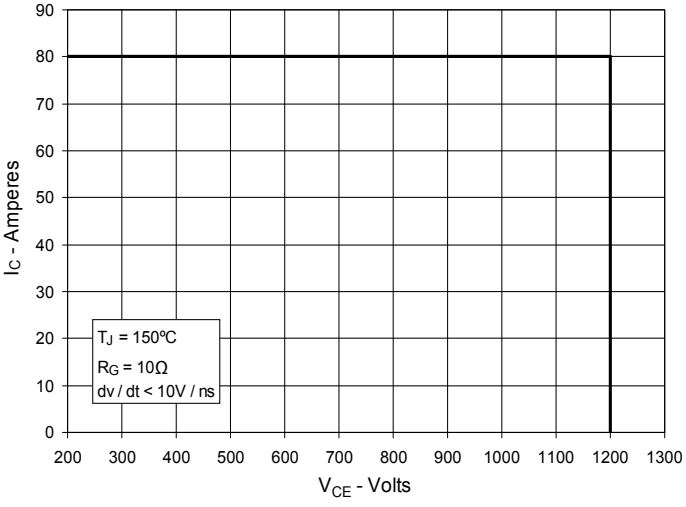
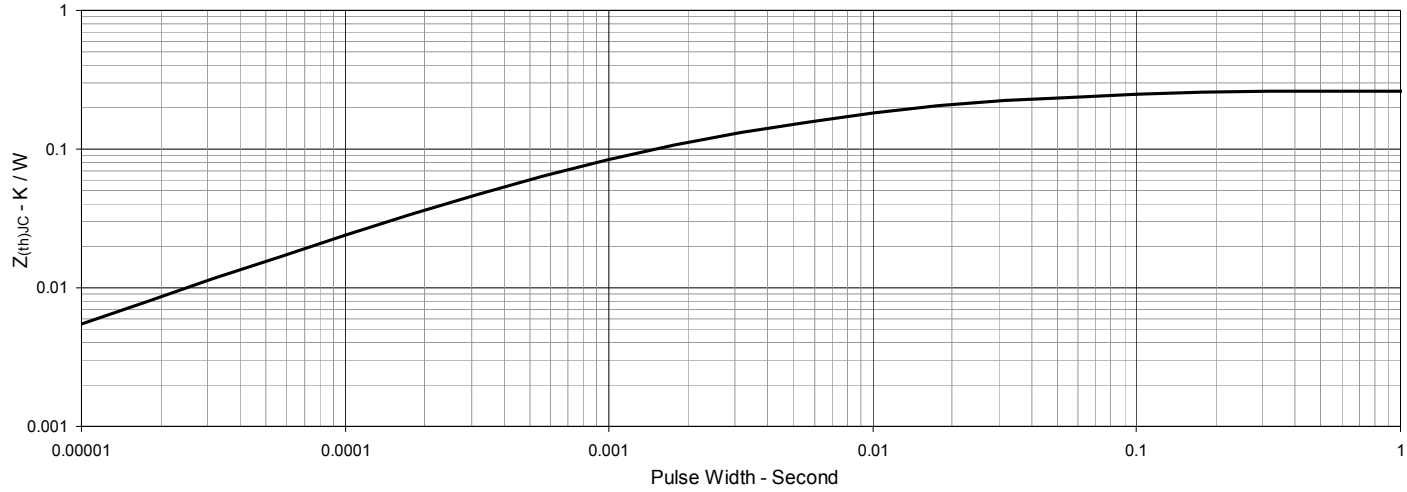


Fig. 11. Maximum Transient Thermal Impedance



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Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

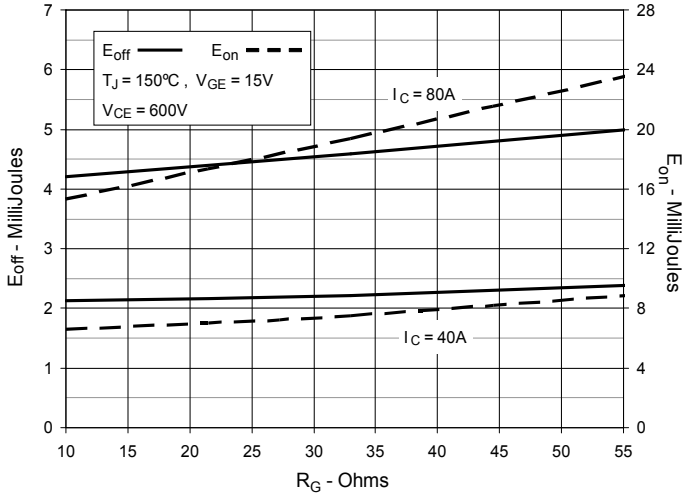


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

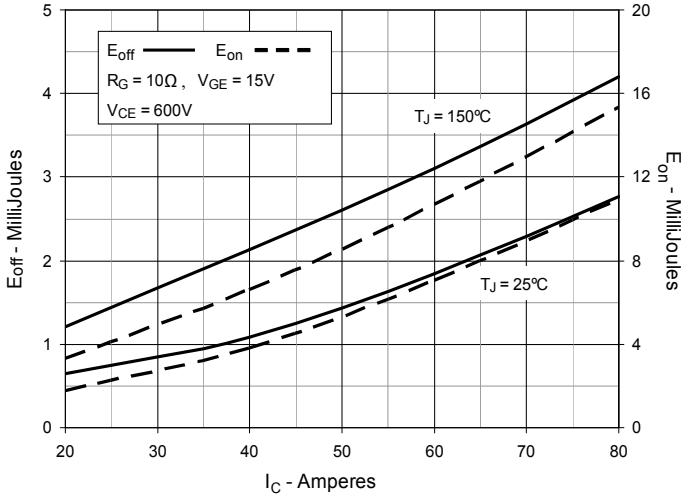


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

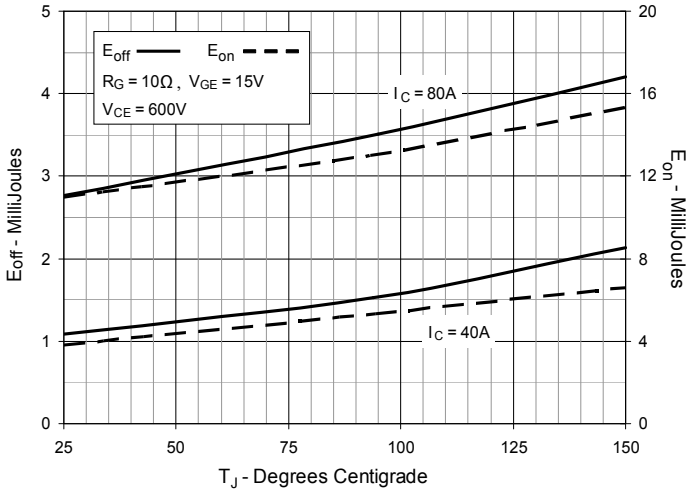


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

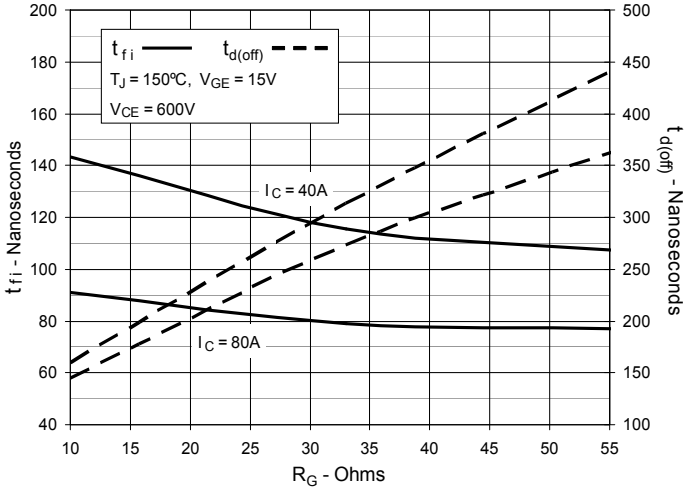


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

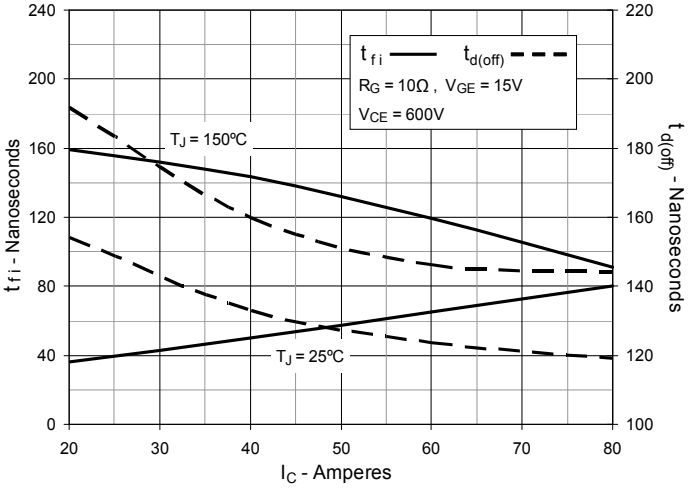
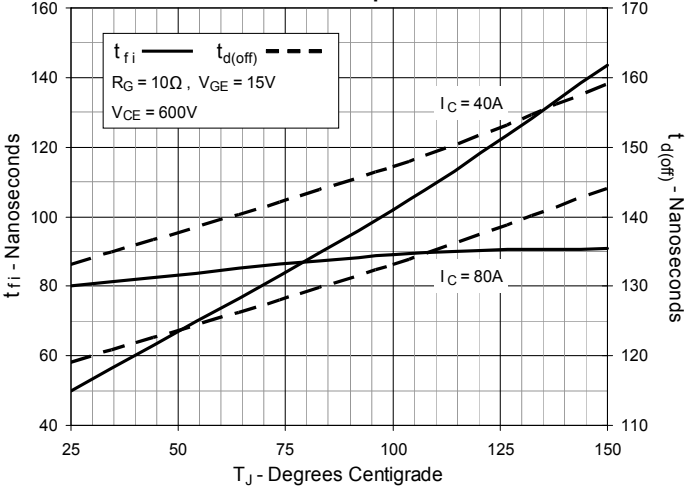


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature



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Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

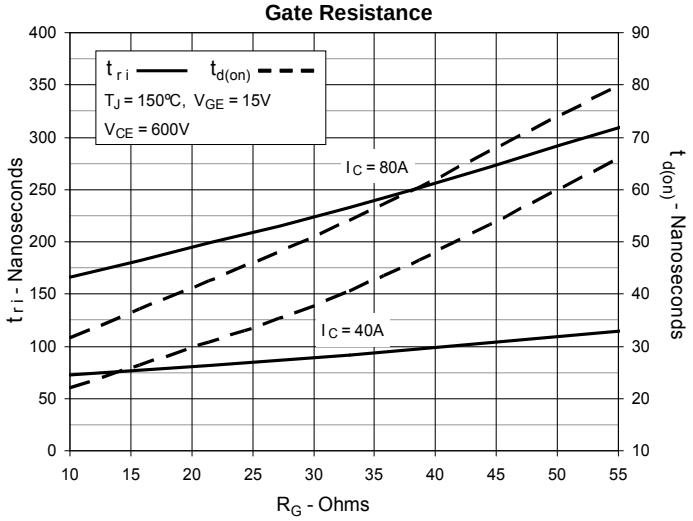


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

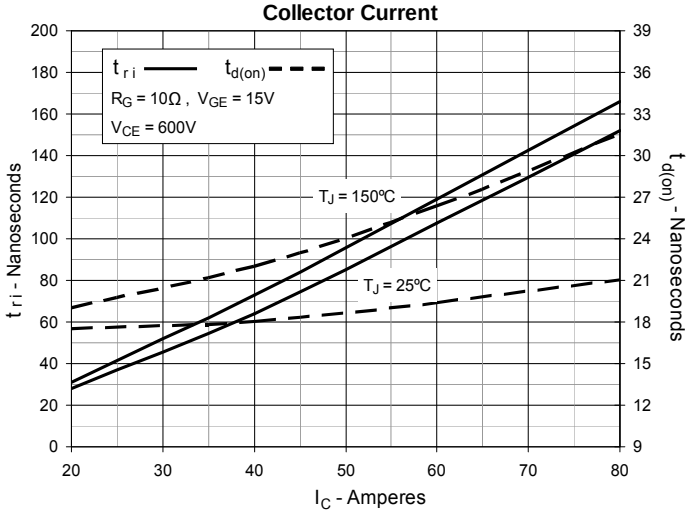
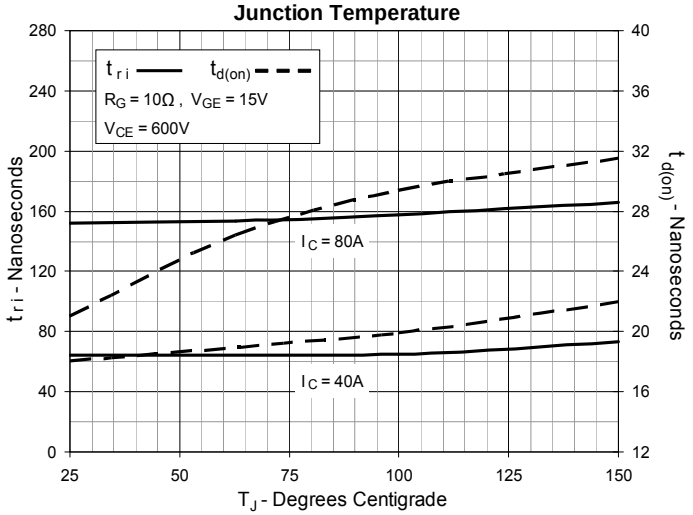


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature





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